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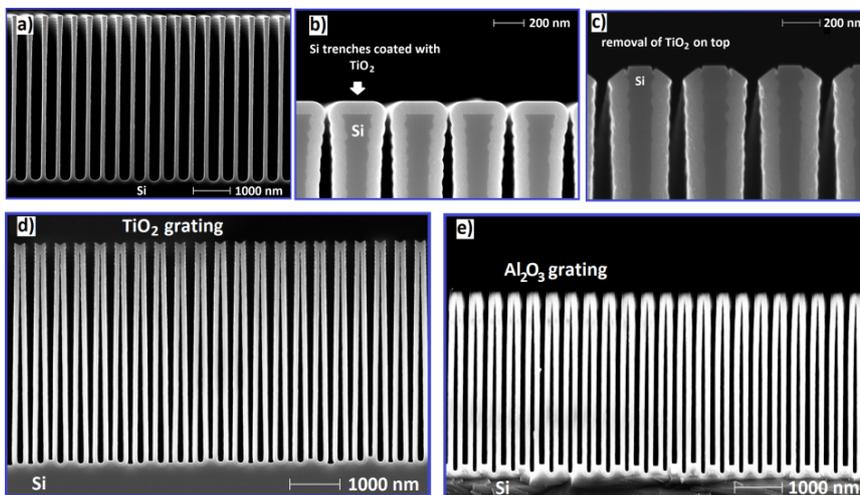
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Fabrication of TiO₂ and Al₂O₃ High Aspect Ratio Nanostructured Gratings at Sub-Micrometer Scale

Evgeniy Shkondin^{a,b}, Jonas Michael Lindhard^b, Mikkel Dysseholm Mar^b, Flemming Jensen^b, Andrei Lavrinenko^a

^aDepartment of Photonics Engineering Technical University of Denmark, DK-2800 Kgs. Lyngby; ^bDanish National Center for Micro- and Nanofabrication (DANCHIP), DK-2800 Kgs. Lyngby. eves@fotonik.dtu.dk

Metal oxides such as TiO₂ and Al₂O₃ can be used for many different fields of applications including photovoltaics, MEMS technology, and high quality dielectrics for DRAM trench capacitors [1]. There is a great need to develop a reliable and reproducible way to pattern such materials on nanoscale. Successful attempts to fabricate and measure 2D photonic crystal based on hexagonal patterning of TiO₂ nanopillars with the aspect ratio of 7.5 have been reported [2]. In this work we present a method of patterning TiO₂ and Al₂O₃ nanogratings with a high aspect ratio of up to 20 on a silicon substrate.



As a starting point deep UV lithography was used to pattern resist on 2 cm² scale chips. Thereafter deep reactive ion etching was used to fabricate 4.5 μm deep silicon trenches with a period of 400 nm (figure 1a). The silicon trenches have been coated using atomic layer deposition (ALD) with 100 nm thick TiO₂ or Al₂O₃ at 150°C (figure 1b). The ALD coatings form nanostructured gratings but in order to isolate the TiO₂/Al₂O₃ trenches it is necessary to remove the silicon core (figure 1b). By introducing a chlorine plasma flow using inductively coupled plasma etching, it is

Figure 1. Fabrication of TiO₂ and Al₂O₃ nanogratings. a) Silicon trenches. b) TiO₂ coverage using ALD. c) Selective opening of TiO₂ top part. d)-e) Isolating TiO₂ or Al₂O₃ by removing the silicon core leads to the formation of nanostructured gratings.

possible to remove the top part of the TiO₂ coating; meanwhile the sidewalls and the bottom remain unharmed (figure 1c). For removal of the Al₂O₃ top part coating, the chlorine plasma was supported by a BCl₃ gas flow. The selective removal of the TiO₂/Al₂O₃ top part provides access to the silicon core between the ALD grown sidewalls. An SF₆ plasma removes selectively silicon without any observable influence on TiO₂ or Al₂O₃ thus revealing a high selectivity throughout the fabrication (figure 1d-e).

Using this procedure the TiO₂ and Al₂O₃ gratings have been fabricated. We believe this approach opens the possibility to fabricate high quality epsilon-near-zero [3] and hyperbolic metamaterials [4], using this procedure.

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